

MMBTA20LT1

General Purpose Amplifier

NPN Silicon

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current – Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

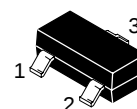
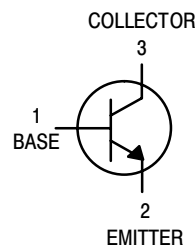
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



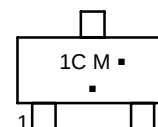
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SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



1C = Specific Device Code

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBTA20LT1	SOT-23	3,000 / Tape & Reel
MMBTA20LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA20LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	40	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	–	Vdc
Collector Cutoff Current ($V_{CB} = 30\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	100	nAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	40	400	–
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	$V_{CE(sat)}$	–	0.25	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = 5.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	125	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	4.0	pF

EQUIVALENT SWITCHING TIME TEST CIRCUITS

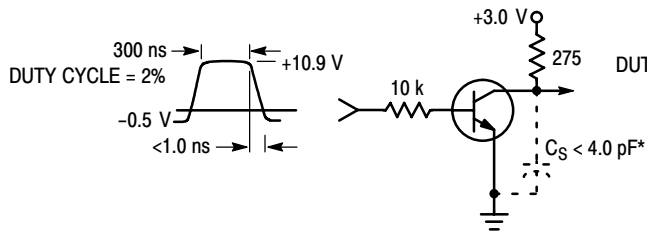


Figure 1. Turn-On Time

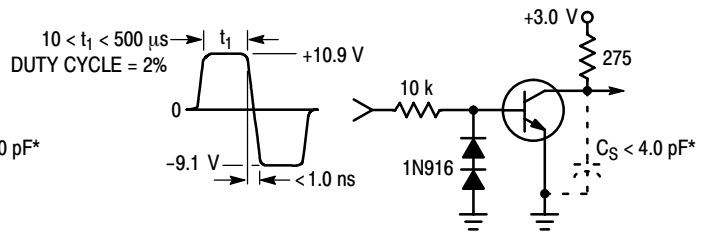


Figure 2. Turn-Off Time

*Total shunt capacitance of test jig and connectors

MMBT20LT1

TYPICAL NOISE CHARACTERISTICS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$)

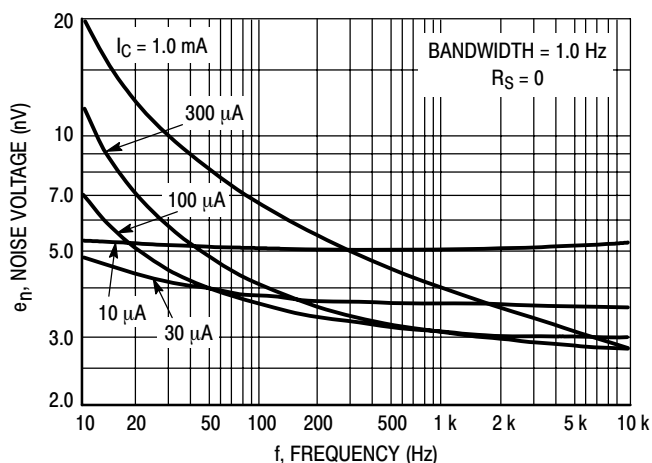


Figure 3. Noise Voltage

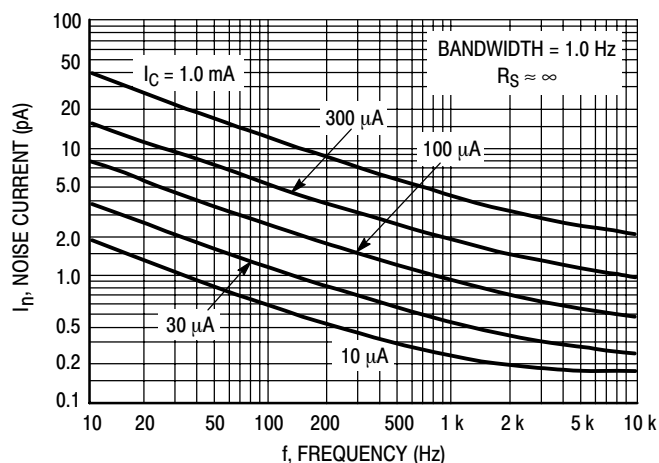


Figure 4. Noise Current

NOISE FIGURE CONTOURS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$)

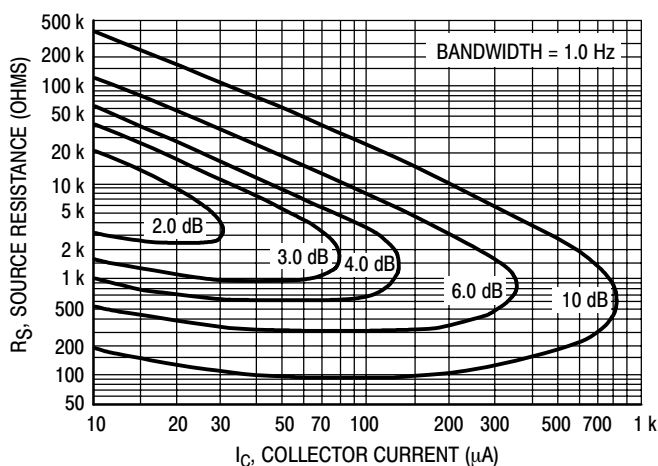


Figure 5. Narrow Band, 100 Hz

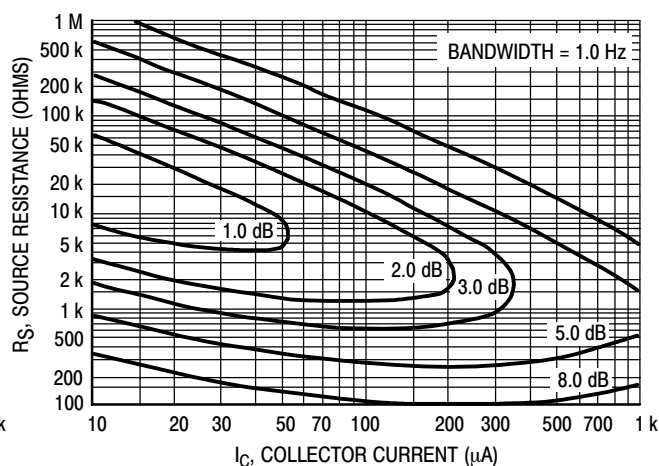


Figure 6. Narrow Band, 1.0 kHz

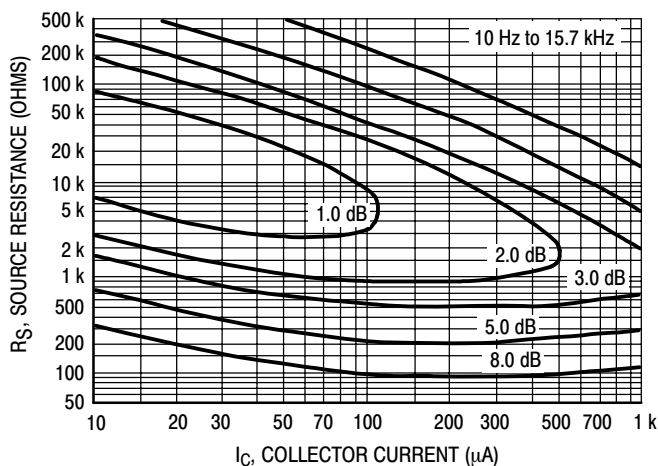


Figure 7. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10} \left(\frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right)^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)

I_n = Noise Current of the Transistor referred to the input. (Figure 4)

K = Boltzman's Constant (1.38×10^{-23} J/°K)

T = Temperature of the Source Resistance (°K)

R_S = Source Resistance (Ohms)

MMBTA20LT1

TYPICAL STATIC CHARACTERISTICS

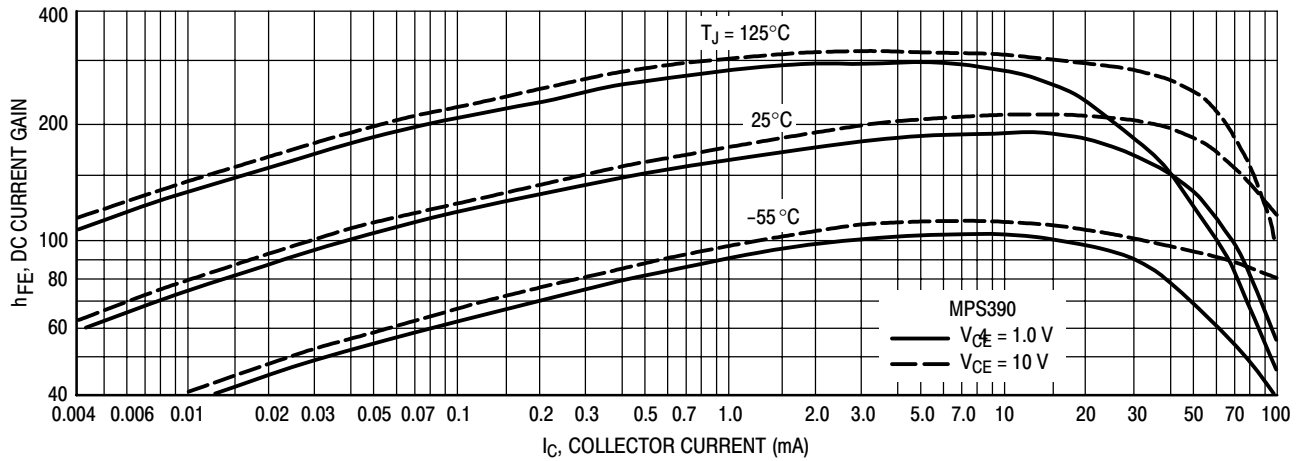


Figure 8. DC Current Gain

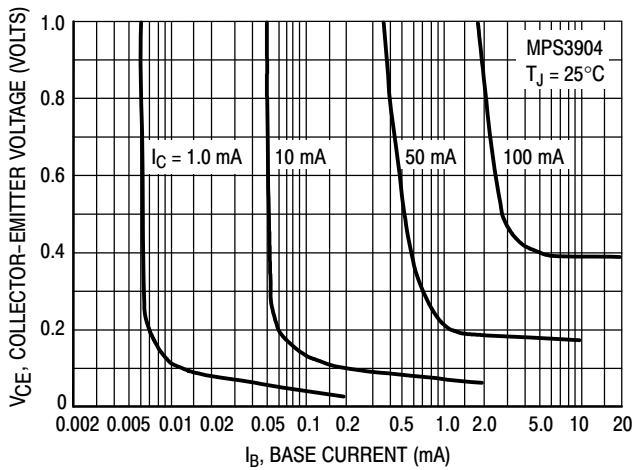


Figure 9. Collector Saturation Region

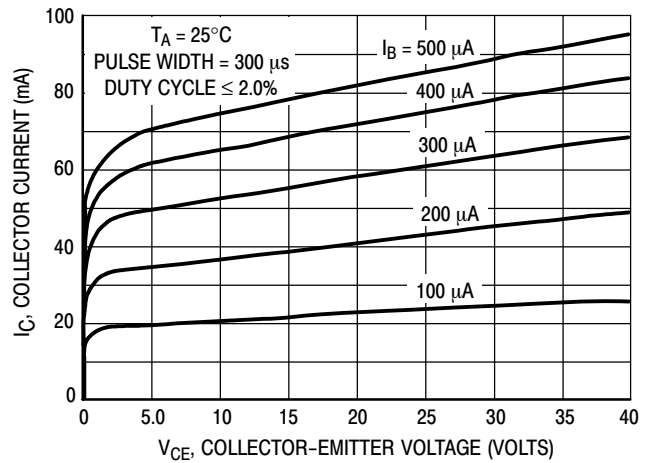


Figure 10. Collector Characteristics

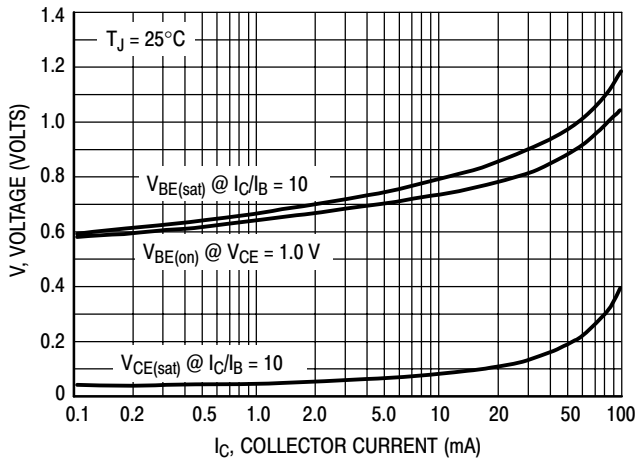


Figure 11. "On" Voltages

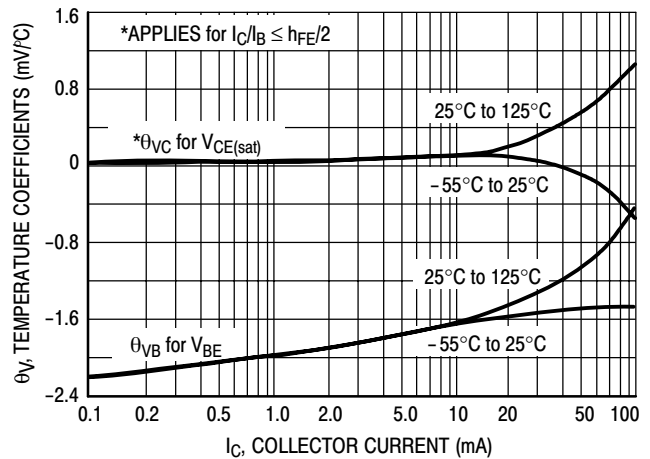


Figure 12. Temperature Coefficients

TYPICAL DYNAMIC CHARACTERISTICS

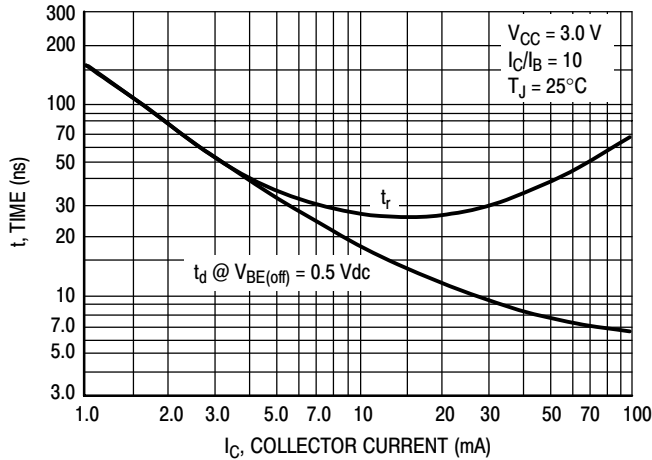


Figure 13. Turn-On Time

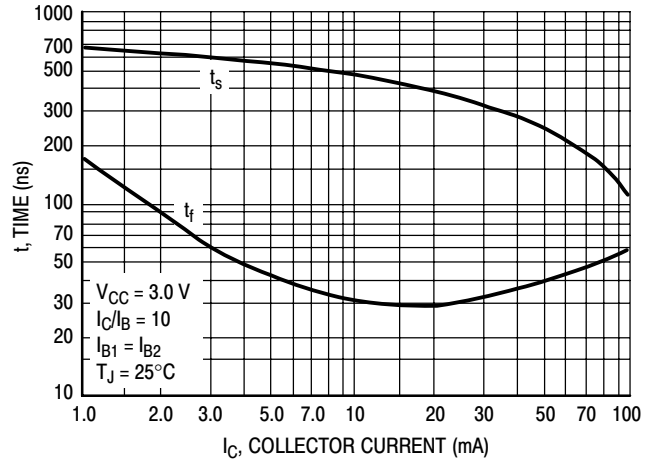


Figure 14. Turn-Off Time

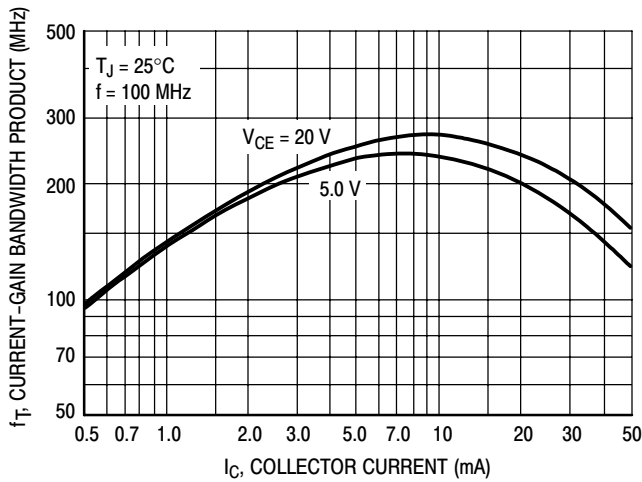


Figure 15. Current-Gain — Bandwidth Product

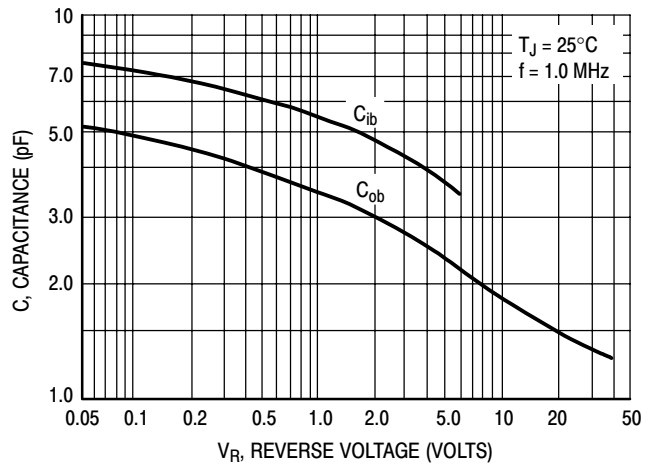


Figure 16. Capacitance

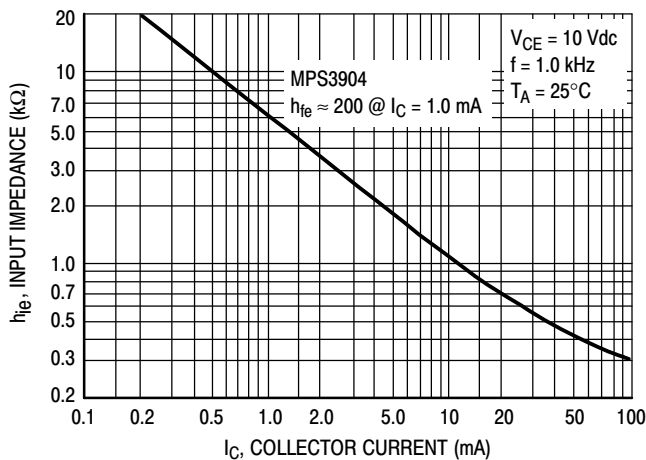


Figure 17. Input Impedance

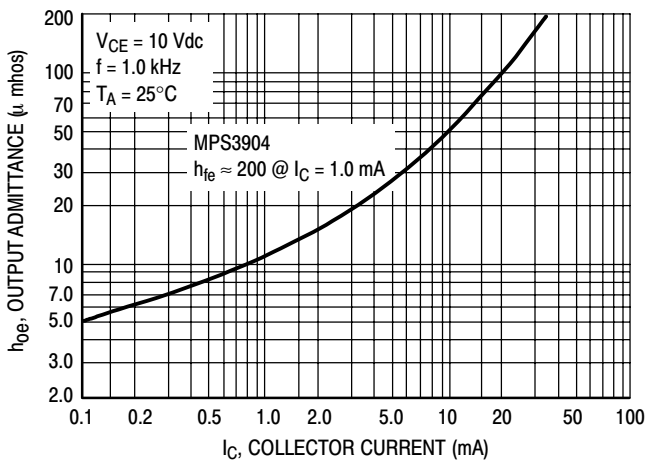


Figure 18. Output Admittance

MMBTA20LT1

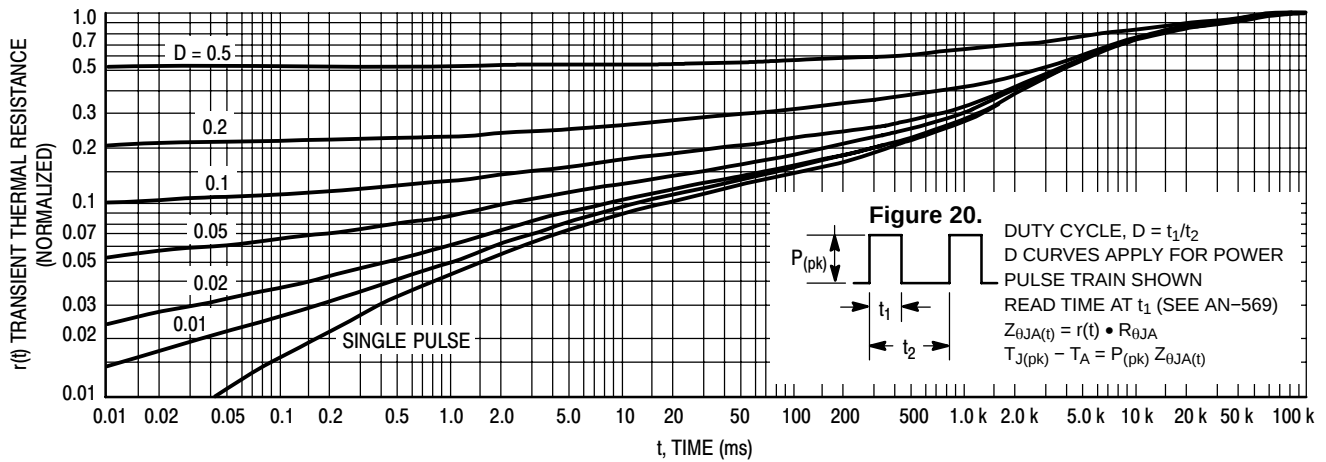


Figure 19. Thermal Response

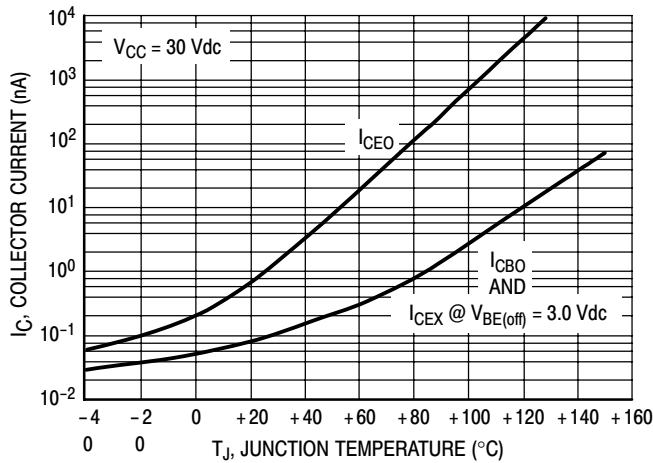


Figure 21.

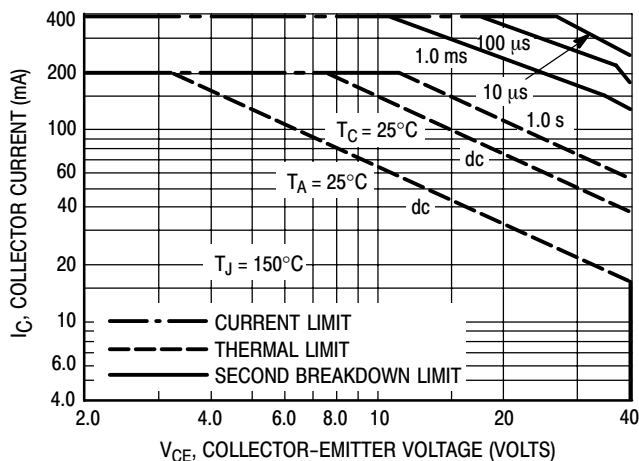


Figure 22.

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 20. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 19 by the steady state value $R_{\theta JA}$.

Example:

The MPS3904 is dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0$ ms, $t_2 = 5.0$ ms. ($D = 0.2$)

Using Figure 19 at a pulse width of 1.0 ms and $D = 0.2$, the reading of $r(t)$ is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

For more information, see AN-569.

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 22 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

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SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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